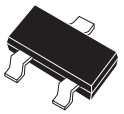
查询CMPD2003供应商

CMPD2003
CMPD2004
CMPD2004S

HIGH VOLTAGE SWITCHING DIODE

Central™ Semiconductor Corp.



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPD2003, CMPD2004, CMPD2004S types are silicon switching diodes manufactured by the epitaxial planar process, designed for applications requiring high voltage capability.

The following configurations are available:

CMPD2003	SINGLE	**MARKING CODE: A82**
CMPD2004	SINGLE	**MARKING CODE: D53**
CMPD2004S	DUAL, IN SERIES	**MARKING CODE: DB6**

MAXIMUM RATINGS (T_A=25°C)

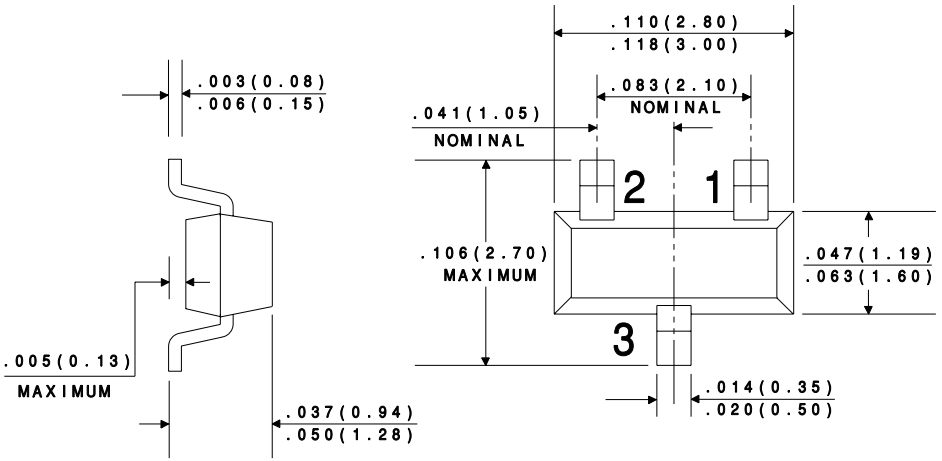
	SYMBOL	CMPD2003	CMPD2004 CMPD2004S	UNITS
Continuous Reverse Voltage	V_R	200	240	V
Peak Repetitive Reverse Voltage	V_{RRM}	250	300	V
Peak Repetitive Reverse Current	I_O	200	200	mA
Continuous Forward Current	I_F	250	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	625	mA
Forward Surge Current, tp=1 μs	I_{FSM}	4000	4000	mA
Forward Surge Current, tp=1 s	I_{FSM}	1000	1000	mA
Power Dissipation	P_D	350		mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150		°C
Thermal Resistance	Θ_{JA}	357		°C/W

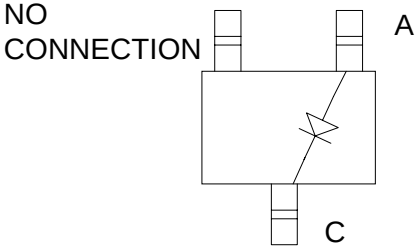
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

		CMPD2003		CMPD2004 CMPD2004S		
SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**MIN**	**MAX**	**UNIT**
B_{VR}	I_R=100 μA	250		300		V
I_R	V_R=200V		100		-	nA
I_R	V_R=200V, T_A=150°C		100		-	μA
I_R	V_R=240V		-		100	nA
I_R	V_R=240V, T_A=150°C		-		100	μA
V_F	I_F=100mA		1.0		1.0	V

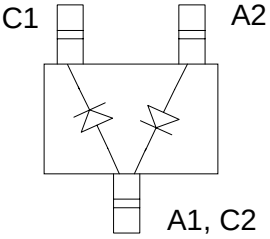
SYMBOL	TEST CONDITIONS	CMPD2003 MIN	CMPD2003 MAX	CMPD2004 CMPD2004S MIN	CMPD2004 CMPD2004S MAX	UNIT
V_F	I_F=200mA		1.25		-	V
C_T	V_R=0, f=1 MHz		5.0		5.0	pF
t_{rr}	I_F=I_R=30mA, RECOV. TO 3.0mA, R_L=100Ω		50		50	ns

All dimensions in inches (mm).





CMPD2003
CMPD2004



CMPD2004S

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